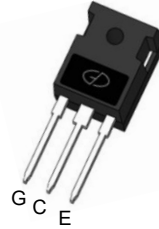


80A,700V Insulated Gate Bipolar Transistor

Features

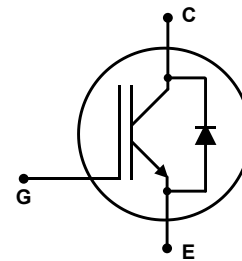
- Trench FS technology offering
- High speed switching
- Low gate charge and VCE(sat)
- High ruggedness, temperature stable behavior
- Maximum junction temperature 175°C



TO-247

Applications

- Solar Inverters
- Uninterruptible power supplies
- Motor drives
- Air condition



Absolute Maximum Ratings (@T_J=25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Collector-Emitter Voltage	V _{CES}	700	V
Gate- Emitter Voltage	V _{GES}	±30	V
Collector Current	I _C	160	A
Collector Current @TC = 100 °C		80	
Pulsed Collector Current, tp limited by Tjmax	I _{Cpuls}	320	A
Diode Continuous Forward Current @T _C = 25 °C	I _F	160	A
Diode Continuous Forward Current @T _C = 100 °C		80	
Power Dissipation @ TC = 25°C	P _D	469	W
Power Dissipation @ TC = 100°C		234	
Operating Junction	T _J	-55 to +175	°C
Storage Temperature Range	T _{STG}	-55 to +175	°C

Thermal Characteristics			
Parameter	Symbol	Max	Unit
Thermal Resistance ,Junction-to-Ambient	$R_{\theta JA}$	40	$^{\circ}C/W$
Thermal Resistance Junction-to-Case for IGBT	$R_{\theta JC}$	0.32	$^{\circ}C/W$
Thermal Resistance Junction-to-Case for Diode	$R_{\theta JC}$	0.44	$^{\circ}C/W$

Electrical Characteristics (@T _J =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	V _{GE} =0V, I _{CE} =1mA	700	--	--	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =80A, V _{GE} =15V	--	1.6	1.85	V
Gate Threshold Voltage	V _{GE(th)}	I _C =250uA, V _{CE} =V _{GE}	4.5	--	6.5	V
Collector-Emitter Leakage Current	I _{CES}	V _{GE} =0V, V _{CE} =700V	--	--	1	μA
Gate to Emitter Reverse Leakage	I _{GES}	V _{GE} =20V, V _{CE} =0V	--	--	100	nA
		V _{GE} =-20V, V _{CE} =0V	--	--	-100	
Input capacitance	C _{ies}	V _{GS} = 0V, V _{DS} = 25V f = 1MHz	--	7278	--	pF
Output capacitance	C _{oes}		--	248	--	
Reverse transfer capacitance	C _{res}		--	151	--	
Turn-on delay time	t _{d(on)}		--	56	--	
Rise time	t _r	V _{CC} =400V, I _C =80A, V _{GE} =0/15V, R _g =10Ω	--	82	--	ns
Turn-Off delay time	t _{d(off)}		--	318	--	
Fall time	t _f		--	52	--	
Turn-On Switching Loss	E _{on}		--	3.73	--	
Turn-Off Switching Loss	E _{off}	--	1.72	--		
Total Switching Loss	E _{ts}	--	5.45	--		
Total Gate Charge	Q _g	V _{CC} =480V, I _C =80A, V _{GE} =15V	--	220	--	nC
Gate to Emitter Charge	Q _{ge}		--	50	--	
Gate to Collector Charge	Q _{gc}		--	92	--	
Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	I _{C(SC)}	V _{GE} =15V, V _{CC} ≤400V, t _{sc} ≤7μs	--	660	--	A

Electrical Characteristics of the Diode (@T _J =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	V _{FM}	I _F =80A	--	1.72	3	V
Reverse Recovery Time	t _{rr}	I _F =80A, V _R =400V V _{GE} =0/15V	--	162	--	ns
Reverse Recovery Charge	Q _{rr}		--	1.53	--	μC
Diode Peak Reverse Recovery Current	I _{RRM}		--	16.3	--	A

Ratings and Characteristics Curves

($T_A = 25^\circ\text{C}$ unless otherwise noted)

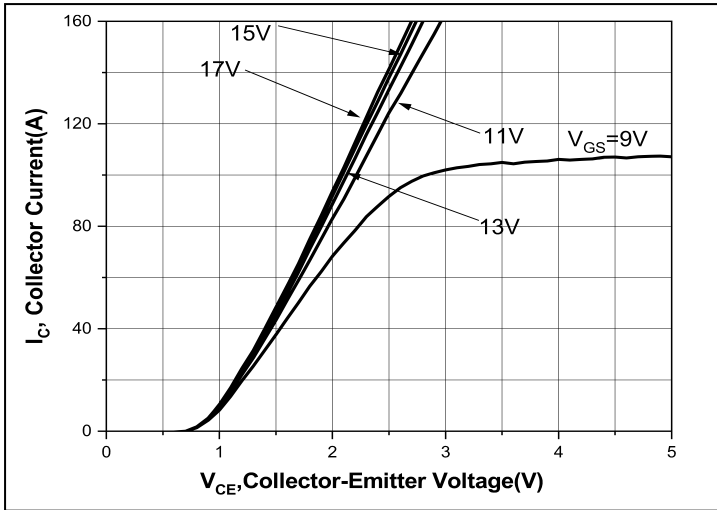


Figure1. Typical Output Characteristics

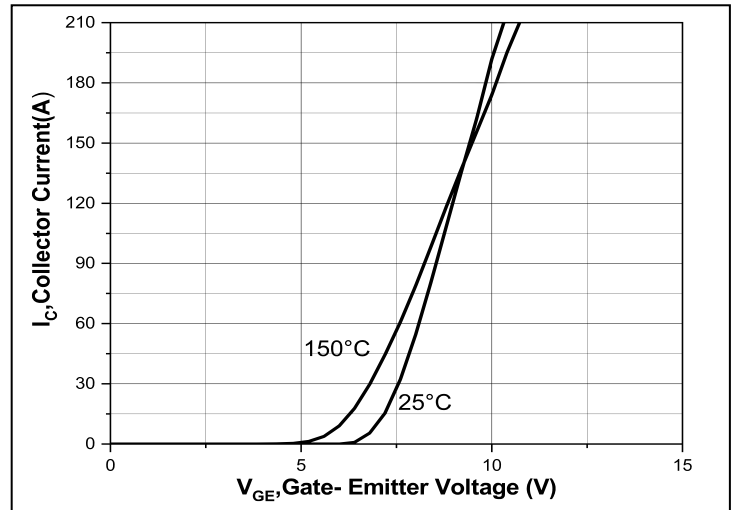


Figure2. Typical Transfer Characteristics

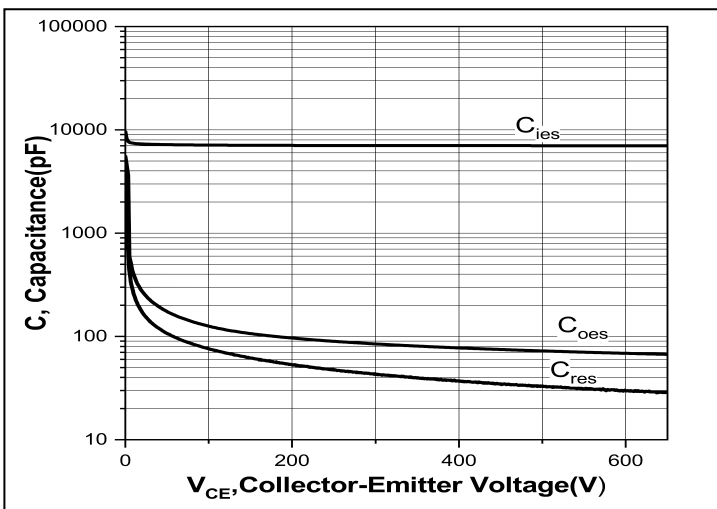


Figure3. Typical Capacitance

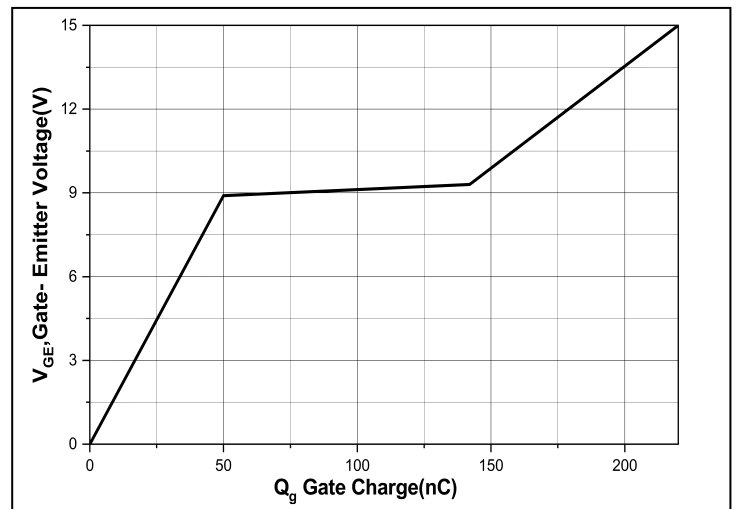


Figure4. Typical Gate Charge

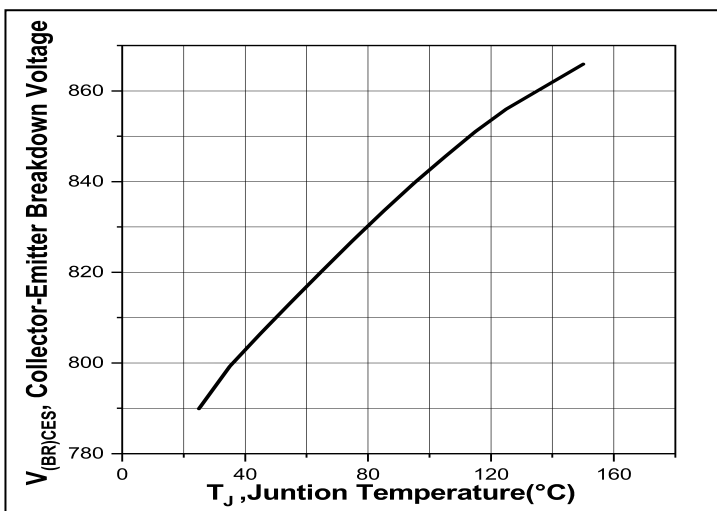


Figure5. Collector-Emitter Breakdown Voltage vs. Temperature

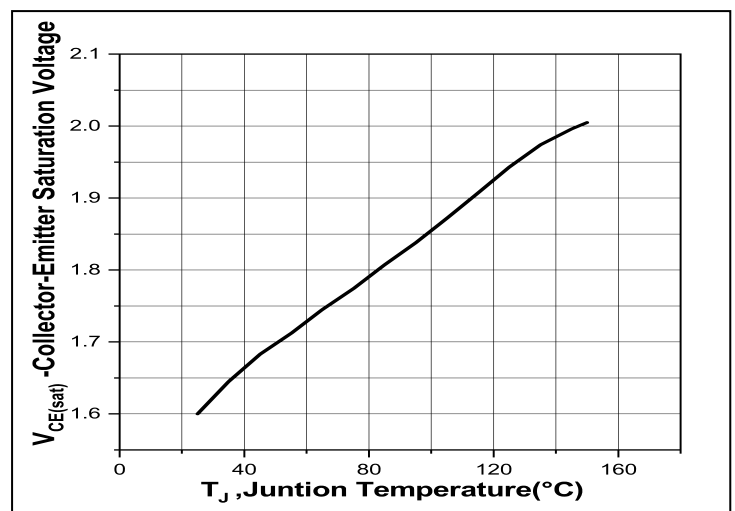


Figure6. Collector-Emitter Saturation Voltage vs. Temperature

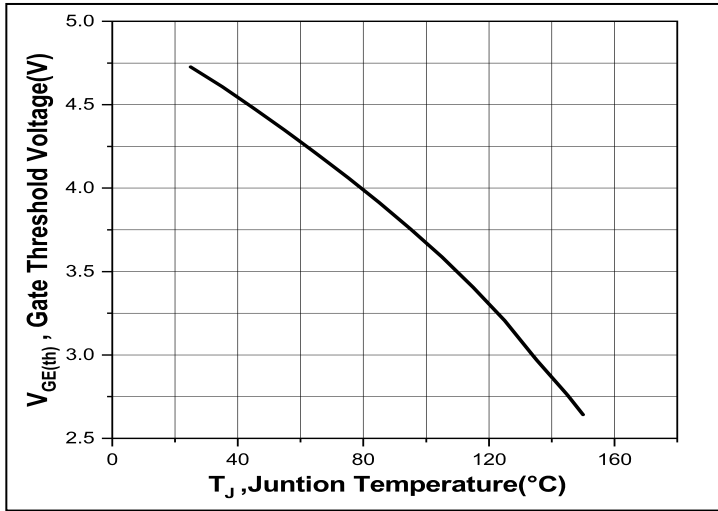


Figure7. Gate Threshold Voltage vs. Temperature

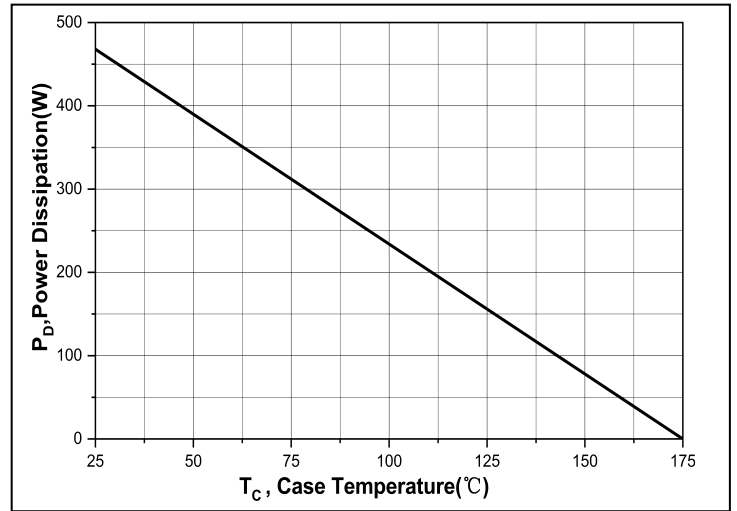


Figure8. Power Dissipation vs. Case Temperature

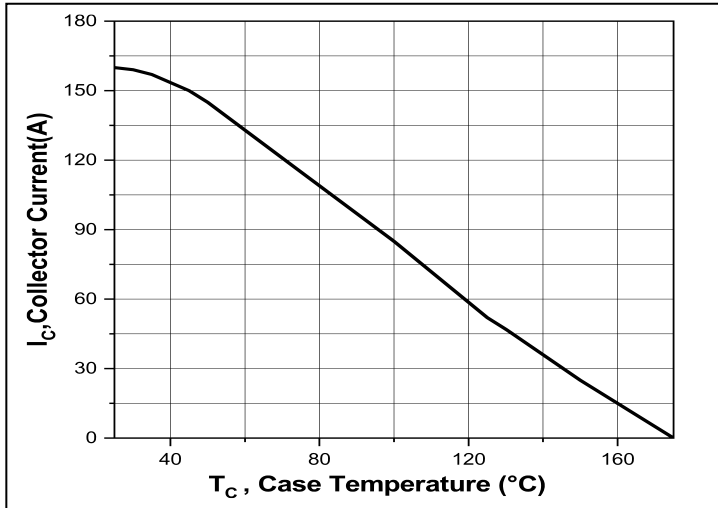


Figure9. Collector Current vs. Temperature

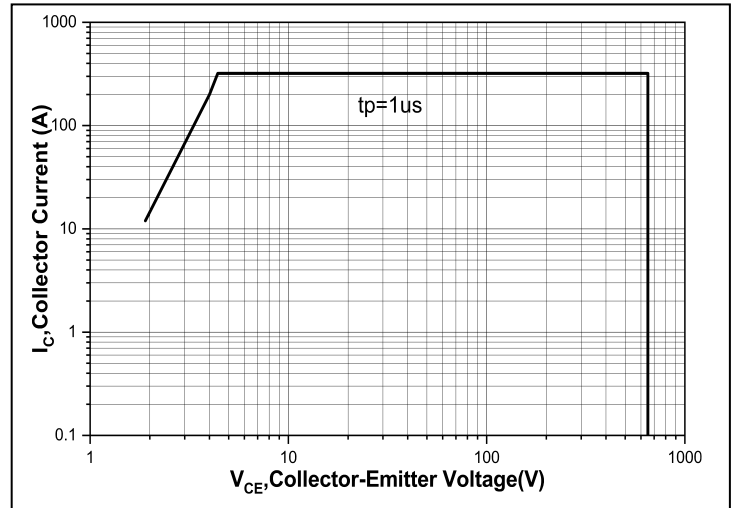
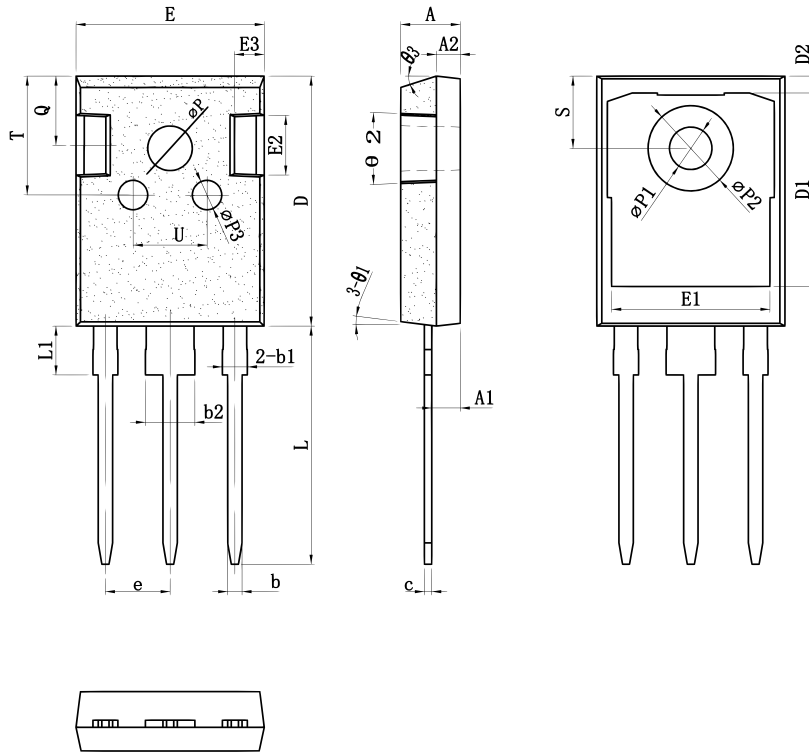


Figure10. Forward Bias Safe Operating Area

Package Outline Dimensions (Unit: millimeters)

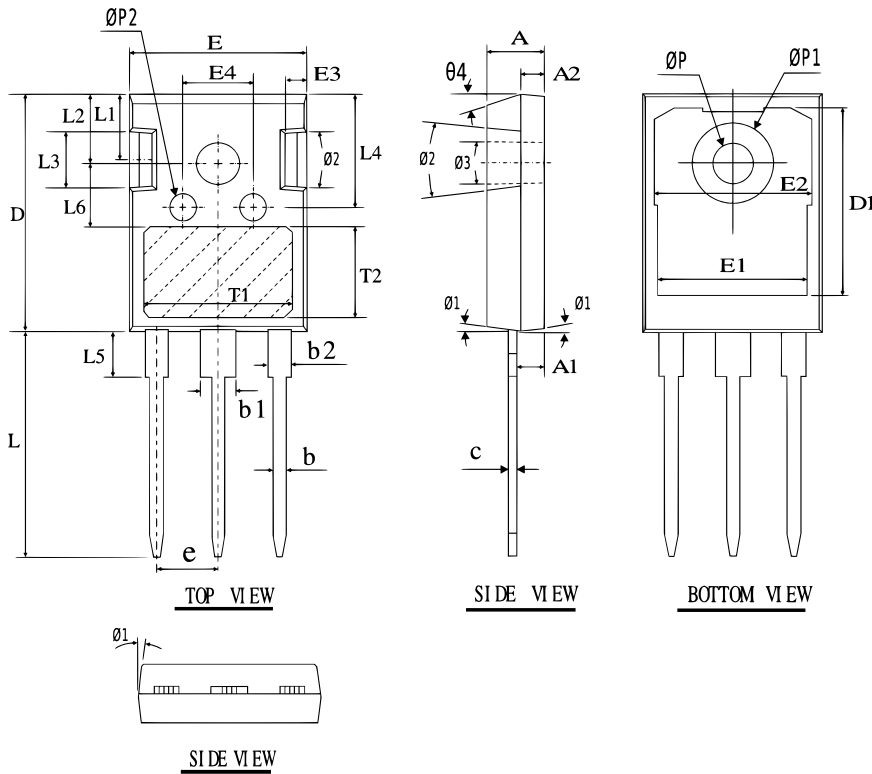
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Option B:



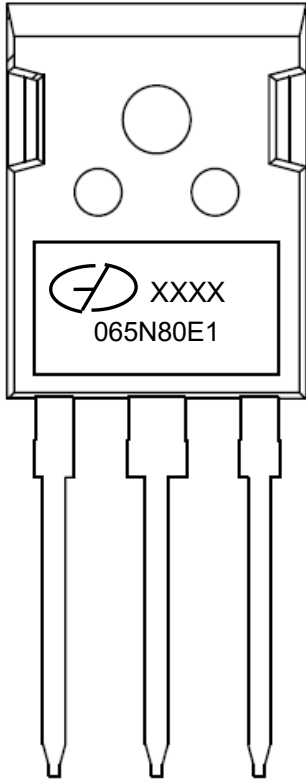
SYMBOL	mm		
	MIN	NOM	MAX
*A	4.90	5.00	5.10
*A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
*b	1.15	1.20	1.25
*b1	1.95	2.10	2.25
*b2	2.95	3.10	3.25
*c	0.55	0.60	0.65
*D	20.90	21.00	21.10
D1	16.35	16.55	16.75
D2	1.05	1.20	1.35
*E	15.70	15.80	15.90
E1	13.10	13.25	13.40
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
*e	5.40	5.44	5.48
*L	19.80	19.98	20.15
*L1	-	-	4.30
* ΦP	3.60	3.70	3.80
* $\Phi P1$	3.45	3.55	3.65
$\Phi P2$	7.03	7.18	7.33
$\Phi P3$	2.40	2.50	2.60
Q	5.60	5.80	6.00
*S	6.05	6.15	6.25
T	9.80	10.00	10.20
U	6.00	6.20	6.40
$\theta 1$	5°	7°	9°
$\theta 2$	1°	3°	5°
$\theta 3$	13°	15°	17°

Option H:




SYMBOL	MN	NOM	MAX
A	4.80	5.00	5.20
A1	2.20	2.40	2.60
A2	1.85	2.00	2.15
b	1.10	1.20	1.30
b1	2.80	3.00	3.20
b2	1.80	2.00	2.20
C	0.52	0.62	0.72
D	20.35	20.65	20.95
D1	16.35	16.55	16.75
E	15.50	15.80	16.10
E1	13.10	13.30	13.50
E2	13.80	14.00	14.20
E3	1.45	1.60	1.75
E4	6.00	6.20	6.40
L	19.80	20.00	20.20
L1	5.88	5.98	6.08
L2	5.88	5.98	6.08
L3	4.90	5.00	5.10
L4	9.70	9.80	9.90
L5	4.10	4.30	4.50
$\theta 1$	4°	7°	10°
$\theta 2$	11°	14°	17°
$\theta 3$	1°	--	2°
$\theta 4$	10°	15°	20°
$\emptyset P$	3.35	3.60	3.85
$\emptyset P1$	--	--	7.30
$\emptyset P2$	2.25	2.50	2.75
e		5.44BSC	
T1		12.80REF	
T2		7.80REF	
L6		5.50REF	

Marking Outline



Part Name: GIT065N80E1

1. Logo Mark: 
2. P/N Mark: 065N80E1
3. Date Code: XXXX

Revision History

Version	Date	Major Changes
Rev.A	2025.01.15	Official Release

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